

Features

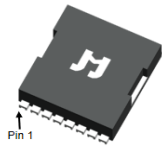
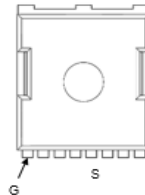
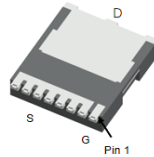
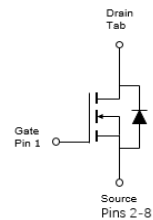
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- Halogen-free; RoHS-compliant

Applications

- Load Switch
- PWM Application
- Power Management

Product Summary

Parameters	Value	Unit
V_{DSS}	80	V
$V_{GS(th_Typ)}$	2.9	V
$I_D (@ V_{GS}=10V)$	454	A
$R_{DS(ON_Typ)} (@ V_{GS}=10V)$	0.82	mΩ


PowerJE@10x12

Pin Assignment

Schematic Diagram
Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH0801NTL-13	SH0801N	1	Tape&Reel	PowerJE@10x12	2000	10000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	80	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	A
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	2143	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	34	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.35	

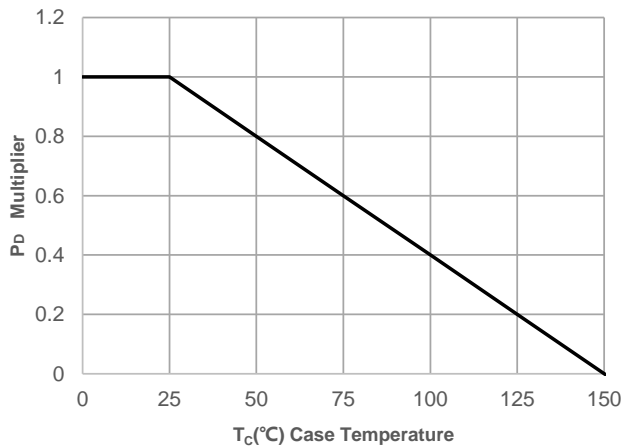
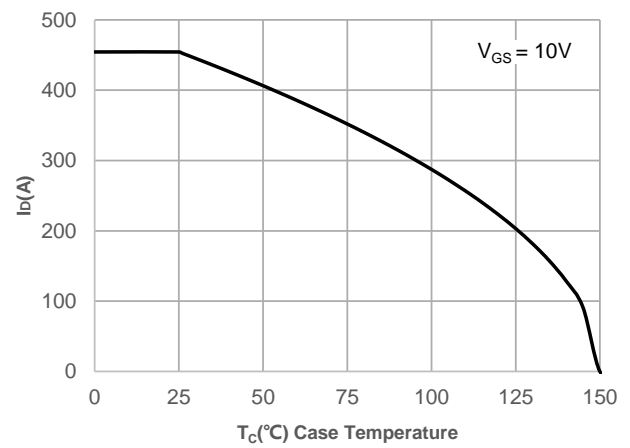
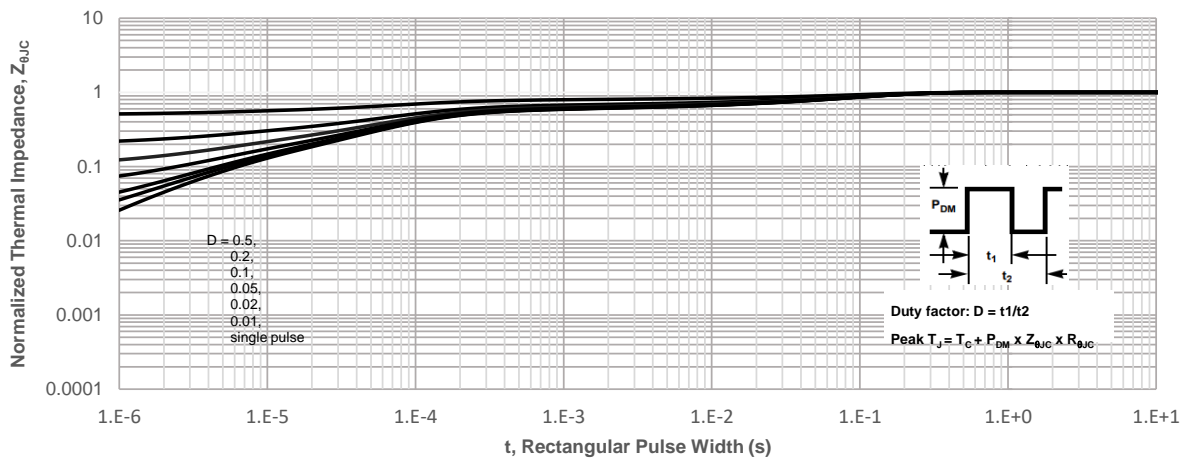
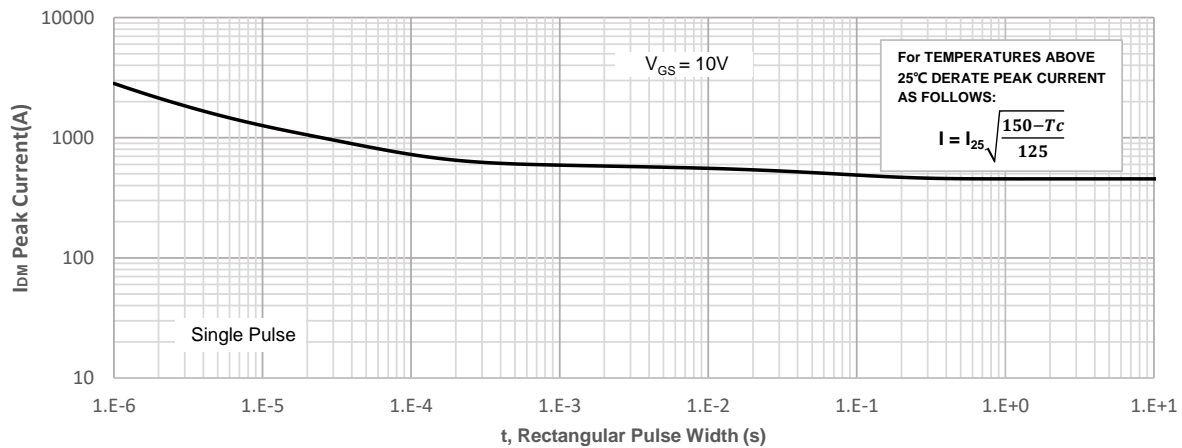
**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	80	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 64V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.1	2.9	3.8	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 10V, I _D = 20A	-	0.82	1.0	mΩ
Dynamic Characteristics						
R _g	Gate Resistance	f = 1MHz	-	4.6	-	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 40V, f = 1MHz	-	14585	21878	pF
C _{oss}	Output Capacitance		-	5456	8185	pF
C _{rss}	Reverse Transfer Capacitance		-	130	261	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 40V, I _D = 20A	-	222	-	nC
Q _{gs}	Gate Source Charge		-	69	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	49	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 40V I _D = 20A, R _{GEN} = 3Ω	-	37	-	ns
t _r	Turn-On Rise Time		-	70	-	ns
t _{d(off)}	Turn-Off DelayTime		-	195	-	ns
t _f	Turn-Off Fall Time		-	102	-	ns
Body Diode Characteristics						
I _S	Maximum Continuous Body Diode Forward Current		-	-	454	A
I _{SM}	Maximum Pulsed Body Diode Forward Current		-	-	1818	A
V _{SD}	Body Diode Forward Voltage	V _{GS} = 0V, I _S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I _F = 20A, di/dt = 100A/us	65	131	196	ns
Qrr	Body Diode Reverse Recovery Charge		-	367	-	nC

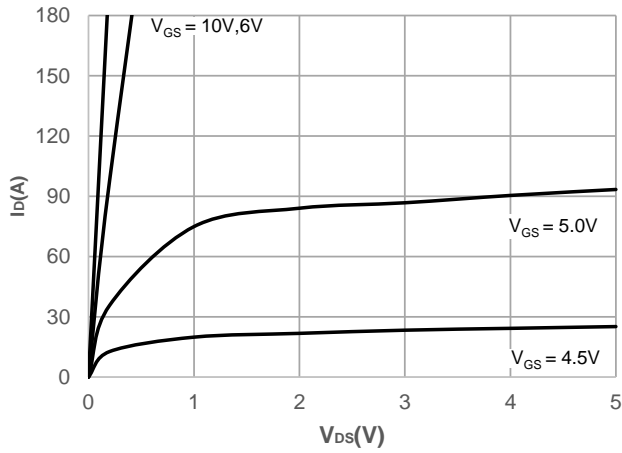
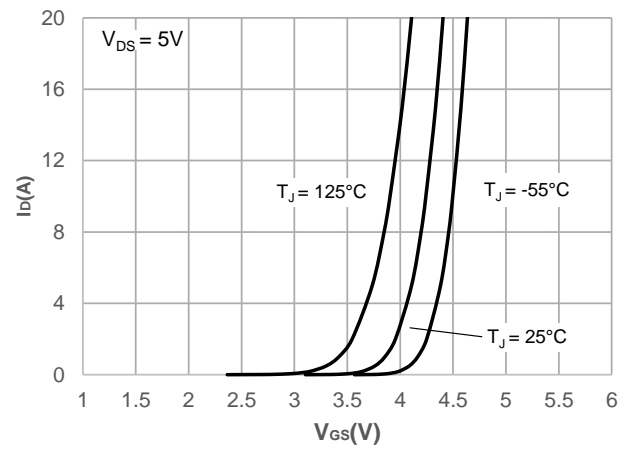
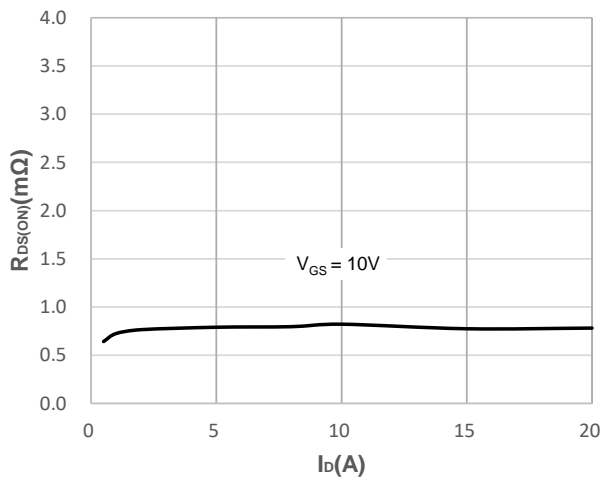
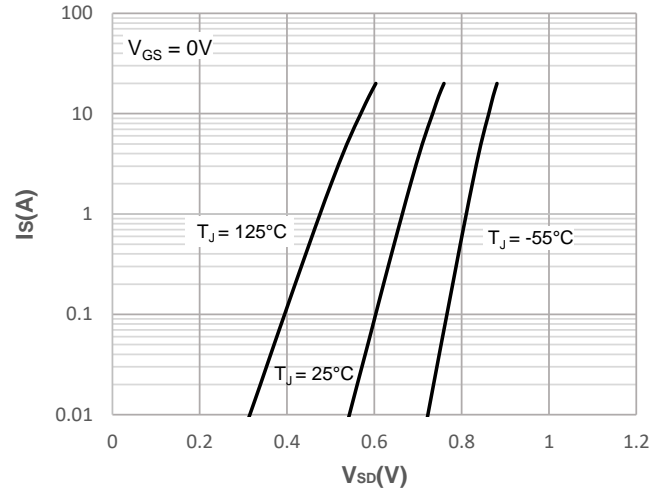
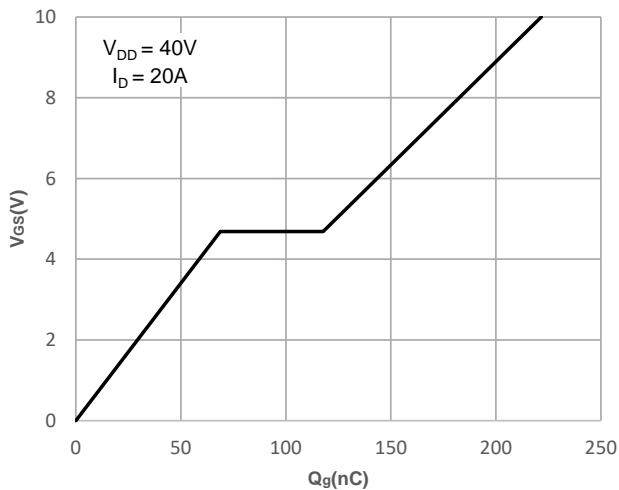
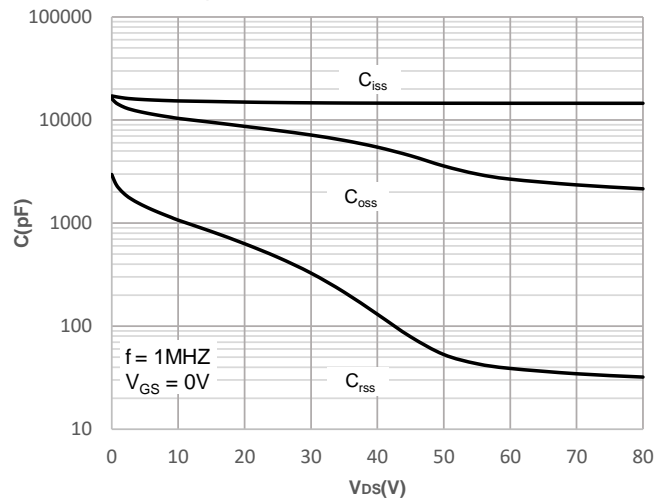
- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 40\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 3\text{mH}$, $I_{AS} = 37.8\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

Figure 2: Current De-rating

Figure 3: Normalized Maximum Transient Thermal Impedance

Figure 4: Peak Current Capacity


Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

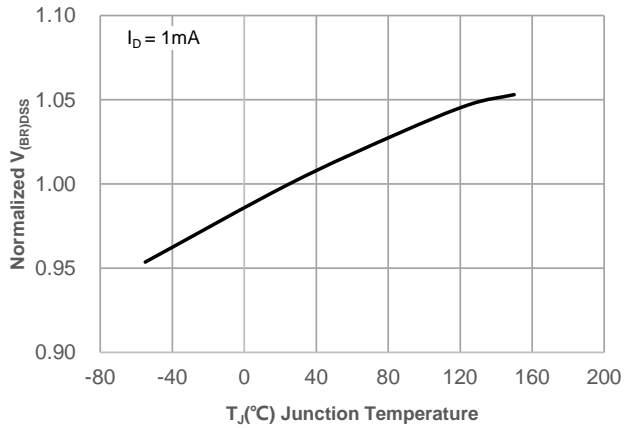


Figure 12: Normalized on Resistance vs. Junction Temperature

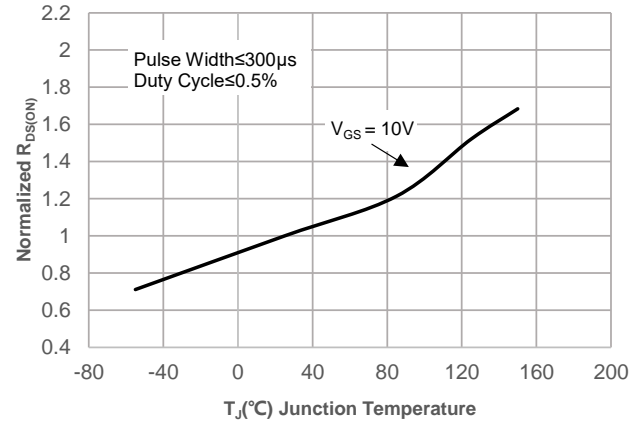


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

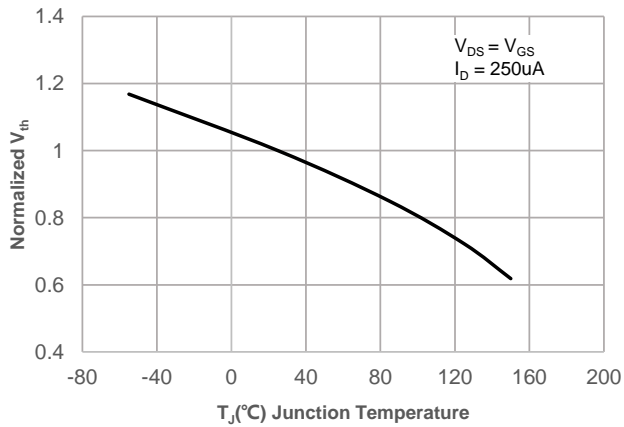


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

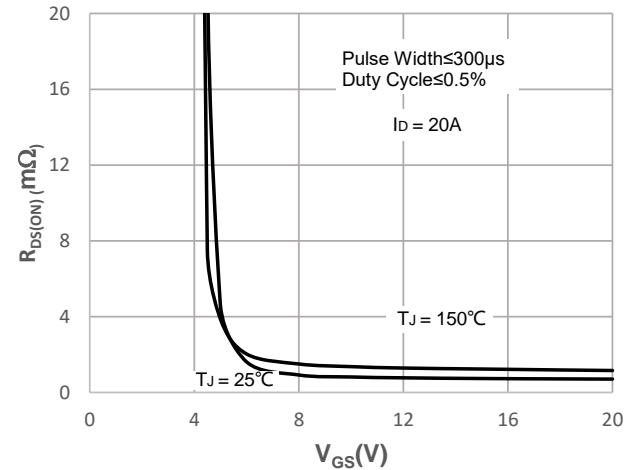
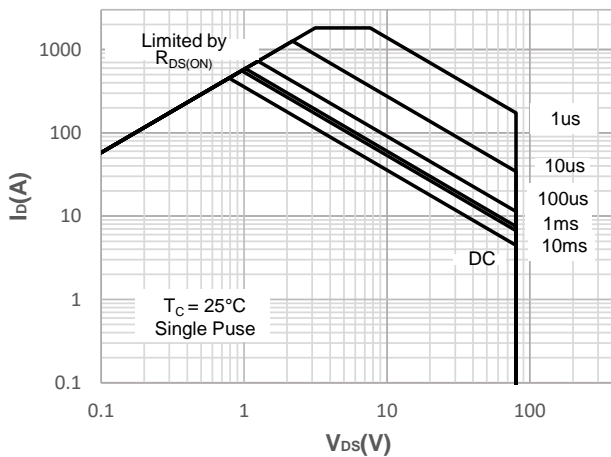


Figure 15: Maximum Safe Operating Area



Test Circuit

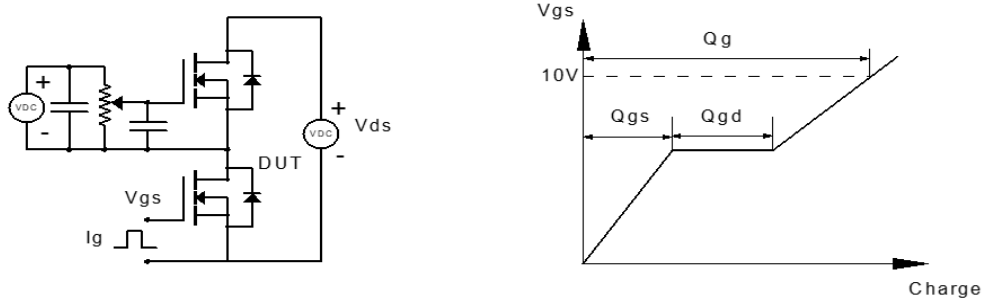


Figure 1: Gate Charge Test Circuit & Waveform

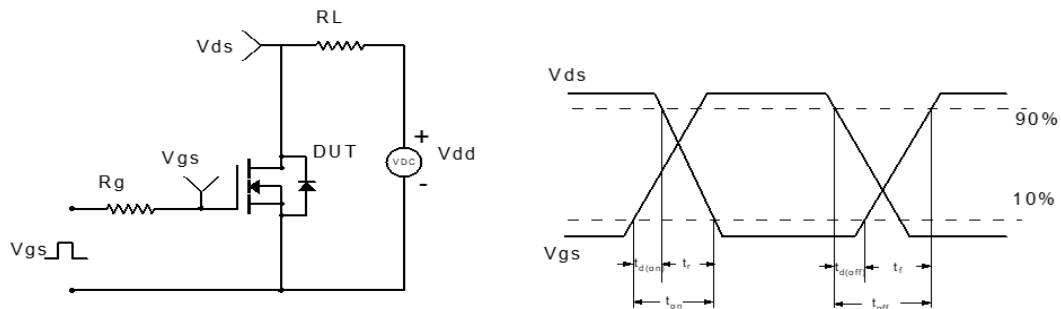


Figure 2: Resistive Switching Test Circuit & Waveform

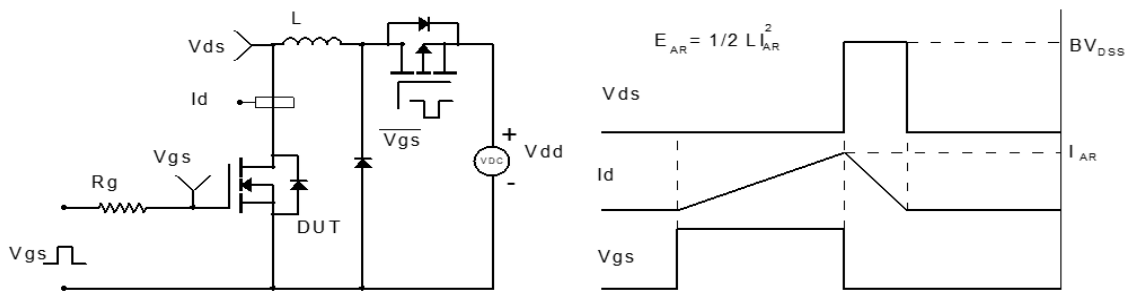


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

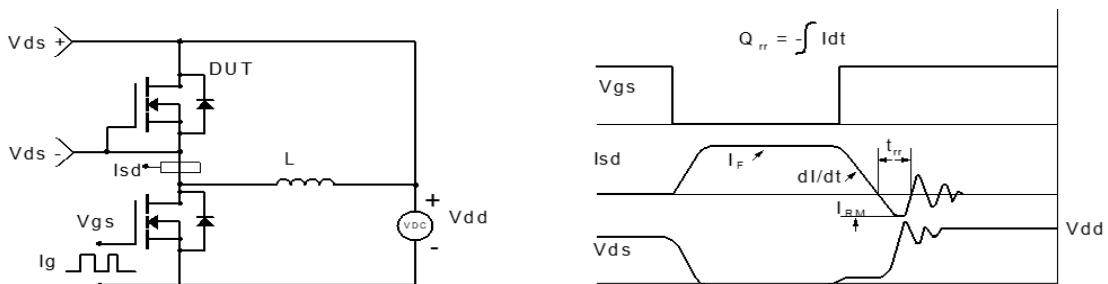
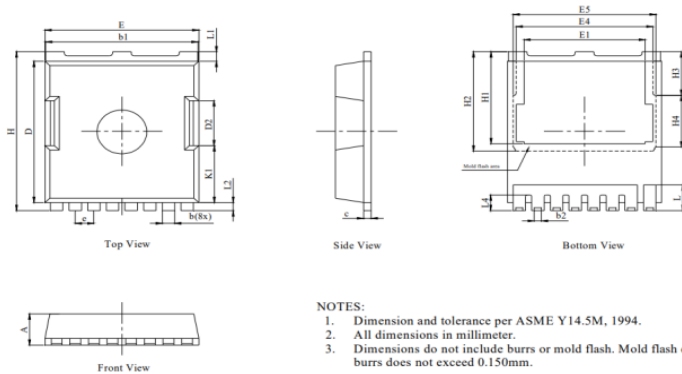


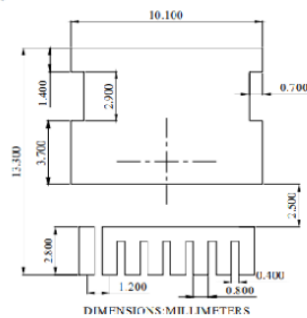
Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PowerJE®10x12)

Package Outlines



Recommended Soldering Footprint



DIM.	MILLIMETER		
	MIN	NOM	MAX
A	2.20	2.30	2.50
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.42	0.46	0.50
C	0.40	0.50	0.65
D	10.28	10.38	10.58
D2	3.30		
E	9.70	9.90	10.10
E1	7.80		
E4	8.80		
E5	9.20		
e	1.20(BSC)		
H	11.48	11.68	11.88
H1	6.55	6.75	6.85
H2	7.30		
H3	3.20		
H4	3.80		
K1	4.18		
L	1.70	1.90	2.10
L1	0.70		
L2	0.60		
L4	1.00	1.15	1.30

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